

SKiiP 802GB061-259CTV

I. Power section

| Absolute maximum ratings | | $T_s = 25^\circ\text{C}$ unless otherwise specified | |
|--------------------------|---|---|-----------------------|
| Symbol | Conditions | Values | Units |
| IGBT | | | |
| V_{CES} | Operating DC link voltage | 600 | V |
| $V_{CC}^{1)}$ | | 400 | V |
| V_{GES} | | ± 20 | V |
| I_C | | $T_s = 25 (70)^\circ\text{C}$ | 800 (600) |
| Inverse diode | | | |
| $I_F = -I_C$ | $T_s = 25 (70)^\circ\text{C}$ | 800 (600) | A |
| I_{FSM} | $T_j = 150^\circ\text{C}$, $t_p = 10\text{ms}$; sin | 8000 | A |
| I^2t (Diode) | Diode, $T_j = 150^\circ\text{C}$, 10ms | 320 | kA^2s |
| $T_j, (T_{stg})$ | AC, 1min. | -40 (-25) ... +150 (125) | $^\circ\text{C}$ |
| V_{isol} | | 2500 | V |

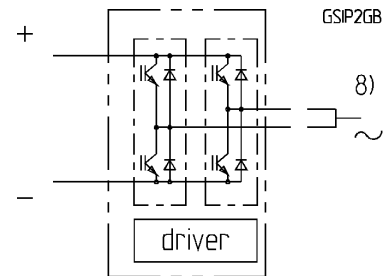
| Characteristics $T_s = 25^\circ\text{C}$ unless otherwise specified | | | | | | | | | |
|--|---|----------------------|-----------|-----------|------------------|-----|------|-------|------|
| Symbol | Conditions | min. | typ. | max. | Units | | | | |
| IGBT | | | | | | | | | |
| V_{CESat} | $I_C = 800\text{A}$, $T_j = 25 (125)^\circ\text{C}$ | - | 2,3 (2,6) | 2,6 | V | | | | |
| V_{CEO} | $T_j = 25 (125)^\circ\text{C}$ | - | 0,8 (0,7) | 1,0 (0,9) | V | | | | |
| r_{CE} | $T_j = 25 (125)^\circ\text{C}$ | - | 1,9 (2,4) | 2,0 (2,5) | $\text{m}\Omega$ | | | | |
| I_{CES} | $V_{GE}=0$, $V_{CE}=V_{CES}$, $T_j=25(125)^\circ\text{C}$ | - | (40) | 0,8 | mA | | | | |
| $E_{on} + E_{off}$ | $I_C=800\text{A}$, $V_{CC}=300\text{V}$ | - | - | 72 | mJ | | | | |
| | $T_j=125^\circ\text{C}$, $V_{CC}=400\text{V}$ | - | - | 105 | mJ | | | | |
| R_{CC-EE} | terminal chip, $T_j = 125^\circ\text{C}$ | - | 0,25 | - | $\text{m}\Omega$ | | | | |
| L_{CE} | top, bottom | - | 7,5 | - | nH | | | | |
| C_{CHC} | per phase, AC-side | - | 1,6 | - | nF | | | | |
| Inverse diode | | | | | | | | | |
| $V_F = V_{EC}$ | $I_F = 800\text{A}$; $T_j = 25(125)^\circ\text{C}$ | - | 1,5 (1,5) | 1,8 | V | | | | |
| V_{TO} | $T_j = 25 (125)^\circ\text{C}$ | - | 0,8 (0,6) | 1,0 (0,8) | V | | | | |
| r_T | $T_j = 25 (125)^\circ\text{C}$ | - | 0,9 (1,1) | 0,9 (1,2) | $\text{m}\Omega$ | | | | |
| E_{RR} | $I_C=800\text{A}$, $V_{CC}=300\text{V}$ | - | - | 26 | mJ | | | | |
| | $T_j=125^\circ\text{C}$, $V_{CC}=400\text{V}$ | - | - | 30 | mJ | | | | |
| Mechanical data | | | | | | | | | |
| M_{dc} | DC terminals, SI Units | 6 | - | 8 | Nm | | | | |
| M_{ac} | AC terminals, SI Units | 13 | - | 15 | Nm | | | | |
| w | SKiiP [®] 2 System w/o heat sink | - | 1,9 | - | kg | | | | |
| w | heat sink | - | 4,7 | - | kg | | | | |
| Thermal characteristics (P16 heat sink; 310 m^3/h); "r" reference to temperature sensor | | | | | | | | | |
| $R_{thjrIGBT}$ | per IGBT | - | - | 0,056 | K/W | | | | |
| $R_{thjrdiode}$ | per diode | - | - | 0,100 | K/W | | | | |
| R_{thra} | per module | - | - | 0,043 | K/W | | | | |
| Z_{th} | R_i (mK/W) (max.) | tau _i (s) | | | | | | | |
| | | 1 | 2 | 3 | 4 | | | | |
| $IGBT_{jr}$ | | 6 | 43 | 7 | - | 1 | 0,13 | 0,001 | - |
| $diode_{jr}$ | | 11 | 77 | 12 | - | 1 | 0,13 | 0,001 | - |
| $heatsink_{ra}$ | | 13,9 | 18,9 | 6,6 | 3,6 | 262 | 50 | 5 | 0,02 |

SKiiP[®] 2

SK integrated intelligent Power 2-pack

SKiiP 802GB061-259CTV

Case S2



Features

- SKiiP technology inside
- low loss IGBTs
- CAL diode technology
- integrated current sensor
- integrated temperature sensor
- integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP[®] 2 System)
- IEC 68T.1 (climate) 40/125/56 (SKiiP[®] 2 power section)

1) with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)

8) AC connection busbars must be connected by the user; copper busbars available on request

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee, expressed or implied is made regarding delivery, performance or suitability.

SKiiP 802GB061-259CTV

SKiiP 2®

SK integrated intelligent Power

SKiiP 802GB061-259CTV

II. Integrated gate driver

| Absolute maximum ratings | | | |
|-------------------------------------|---------------------------------|---------------|-------|
| Symbol | Term | Value | Unit |
| V _{S1} | stabilized 15V power supply | 18 | V |
| V _{S2} | unstabilized 24V power supply | 30 | V |
| V _{iH} | input signal voltage (high) | 15 + 0,3 | V |
| dv/dt | secondary to primary side | 75 | kV/μs |
| V _{isolIO} | input / output (AC) | 2500 | Vac |
| V _{isol12} | output 1 / output 2 (AC) | 1500 | Vac |
| f _{max} | switching frequency | 20 | kHz |
| T _{op} (T _{stg}) | operating / storage temperature | - 25 ... + 85 | °C |

Gate driver features

- CMOS compatible inputs
- wide range power supply
- integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- short circuit protection
- over current protection
- over voltage protection (option)
- power supply protected against under voltage
- interlock of top/bottom switch
- isolation by transformers
- fibre optic interface (option for GB-types only)
- IEC 68T.1 (climate) 25/85/56 (SKiiP® 2 gate driver)

| Electrical characteristics (T _a = 25 °C) | | | | Values | | | | |
|---|---|---|--|--------|------|-----|------|-------|
| Symbol | Term | | | | min | typ | max. | Units |
| V _{S1} | supply voltage stabilized | | | | 14,4 | 15 | 15,6 | V |
| V _{S2} | supply voltage non stabilized | | | | 20 | 24 | 30 | V |
| I _{S1} | V _{S1} = 15V | 210 + 390*f / f _{max} + 1,3* (I _{AC} /A) | | | | | | mA |
| I _{S2} | V _{S2} = 24V | 160 + 290*f / f _{max} + 1,0 * (I _{AC} /A) | | | | | | mA |
| V _{iT+} | input threshold voltage (High) | | | | 11,2 | – | – | V |
| V _{iT-} | input threshold voltage (Low) | | | | – | – | 5,4 | V |
| R _{in} | input resistance | | | | – | 10 | – | kΩ |
| t _{d(on)IO} | turn-on propagation time (system) | | | | – | 1,1 | – | μs |
| t _{d(off)IO} | turn-off propagation time (system) | | | | – | 1,4 | – | μs |
| t _{pERRRESET} | error memory reset time | | | | 9 | – | – | μs |
| t _{TD} | top/bottom switch: interlock time | | | | – | 3,3 | – | μs |
| I _{analogOUT} | 8 V corresponds to | | | | – | 661 | – | A |
| I _{Vs1outmax} | max. current of 15 V supply voltage (available when supplied with 24V) | | | | – | – | 50 | mA |
| I _{A0max} | output current at pin 12/14 | | | | – | – | 5 | mA |
| V _{ol} | logic low output voltage | | | | – | – | 0,6 | V |
| V _{oH} | logic high output voltage | | | | – | – | 30 | V |
| I _{TRIPSC} | over current trip level (I _{analog OUT} = 10V) | | | | – | 826 | – | A |
| I _{TRIPLG} | ground fault protection | | | | – | – | – | A |
| T _{ip} | over temperature protection | | | | 110 | – | 120 | °C |
| U _{DCTRIP} | trip level of U _{DC} -protection (U _{analog OUT} = 9V); (option) | | | | 400 | – | – | V |

For electrical and thermal design support please use SEMISEL. Access to SEMISEL is via SEMIKRON website <http://semisel.semikron.com>. Further questions can be placed via <http://faq.semikron.com/>.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.